

L Number	Hits	Search Text	DB	Time stamp
1	21	(Forming near (NMOS or PMOS)).ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/31 12:53
2	4364	((438/724) or (438/287) or (438/762) or (438/763) or (438/775) or (438/776) or (438/777)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/31 12:54
3	326	((438/724) or (438/287) or (438/762) or (438/763) or (438/775) or (438/776) or (438/777)).CCLS.) and CMOS	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/31 12:54
4	1165	((438/724) or (438/287) or (438/762) or (438/763) or (438/775) or (438/776) or (438/777)).CCLS.) and transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/31 12:54
5	171	((438/724) or (438/287) or (438/762) or (438/763) or (438/775) or (438/776) or (438/777)).CCLS.) and transistor) and (substrate with conductivity)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/31 14:05
6	1219	MOS and transistor and (substrate with conductivity) and (etch\$3 with (gate near oxide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/31 14:06
-	43	Kraft.in. and nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/31 12:49